

FEATURES

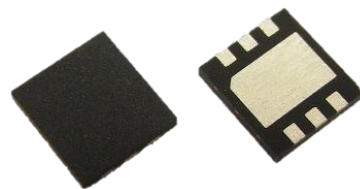
- High Voltage Operation : $V_{DS}=50V$
- High Power : 46dBm (typ.) @ P_{sat}
- High Efficiency : 60% (typ.) @ P_{sat}
- Power Gain : 18.5dB (typ.) @ $f=2.65GHz$
- Proven Reliability

DESCRIPTION

Sumitomo's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use up to 2.8GHz W-CDMA & LTE design requirements as it offers high gain, long term reliability and ease of use.

This device target applications are driver stage and final stage of micro cell base transceiver stations.



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Condition	Rating	Unit
Operating Voltage	V_{DS}		55	V
Drain-Source Voltage	V_{DS}^*	$V_{GS}=-8V$	160	V
Gate-Source Voltage	V_{GS}^*		-15	V
Total Power Dissipation	P_t^*		23.8	W
Storage Temperature	T_{stg}		-40 to +125	deg.C
Channel Temperature	T_{ch}		250	deg.C

* : Case Temperature $T_c=25deg.C$

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V_{DS}		≤ 55	V
Forward Gate Current	I_{GF}	$RG=15ohm$	≤ 76	mA
Reverse Gate Current	I_{GR}	$RG=15ohm$	≥ -1.3	mA
Channel Temperature	T_{ch}		≤ 200	deg.C
Average Output Power	$P_{ave.}$		≤ 43.0	dBm

ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25deg.C$)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	V_p	$V_{DS}=50V, I_{DS}=9mA$	-1.0	-1.5	-2.0	V
Saturated Power	P_{sat}^*1	$V_{DS}=50V,$ $I_{DS}(DC)\approx 0mA$ $f=2.65GHz$	45.0	46.0	-	dBm
Drain Efficiency	DE^*2	$V_{DS}=50V$	11.5	13.5	-	%
Power Gain	G_p^*2	$I_{DS}(DC)\approx 150mA$ $f=2.65GHz$	17.5	18.5	-	dB
Thermal Resistance	R_{th}^*3	Channel to Case at 21W PDC	-	5.5	6.5	deg.C/W

Note : *1 : 10%-duty RF pulse (DC supply constant)

*2 : $P_{out}=32.5dBm$, CW modulation Signal (W-CDMA)

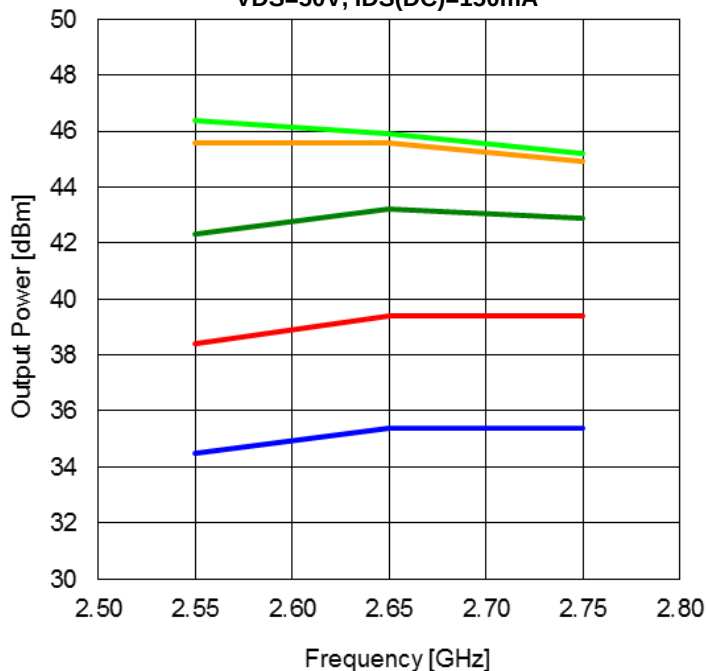
*3 : Sampling Test : samples size 10pcs. Criteria(accept / reject)=(0 / 1)

RoHS COMPLIANCE

Yes

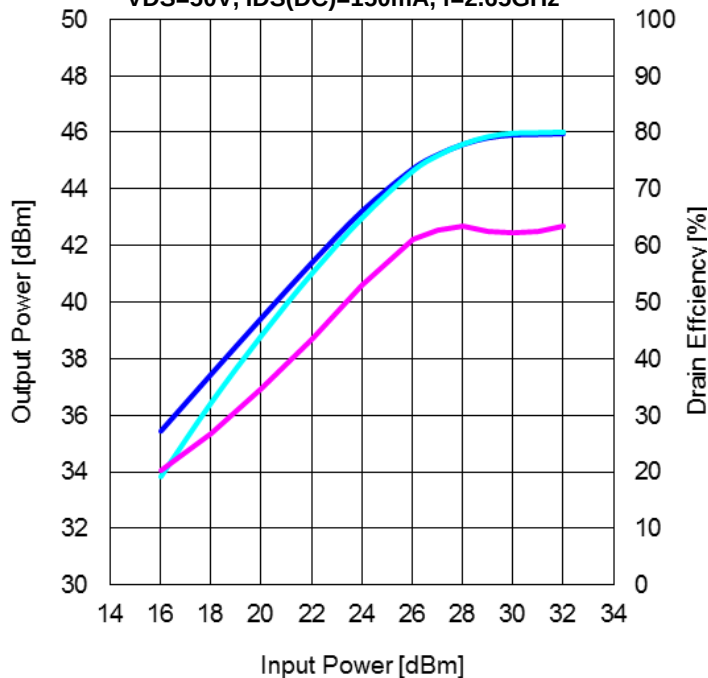
RF characteristics @f=2.65GHz fine tuned

Output Power vs. Frequency VDS=50V, IDS(DC)=150mA



Pin=16dBm Pin=20dBm Pin=24dBm
Pin=28dBm Pin=32dBm

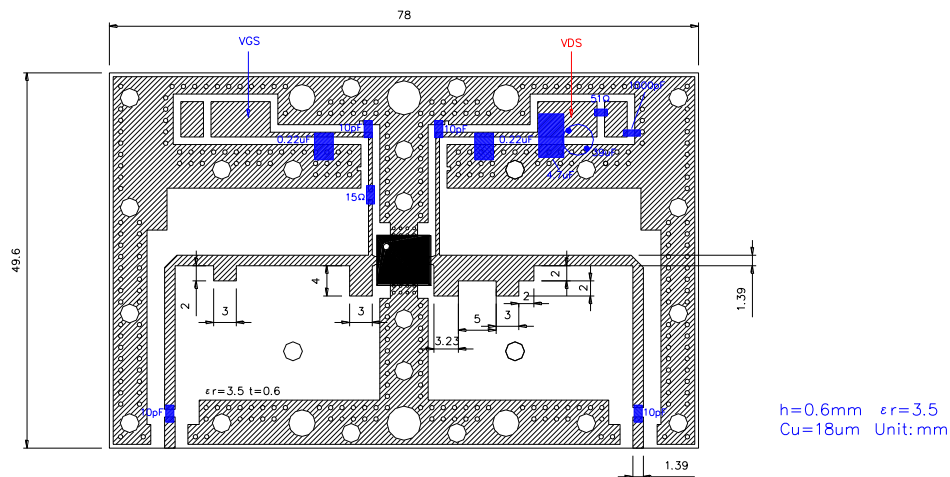
Output Power and Drain Efficiency vs. Input Power
VDS=50V, IDS(DC)=150mA, f=2.65GHz



— Pout (class AB) — Pout (class B) — DE (class B)

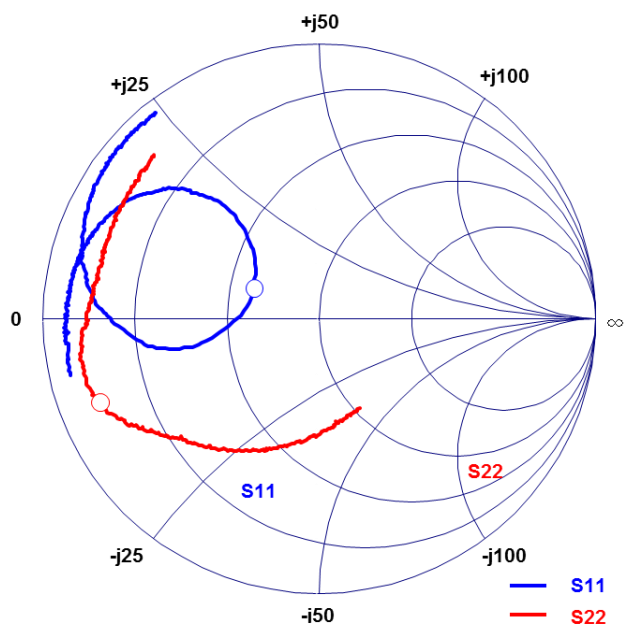
Test Fixture

Pulse Signal (10%-duty, DC : constant)

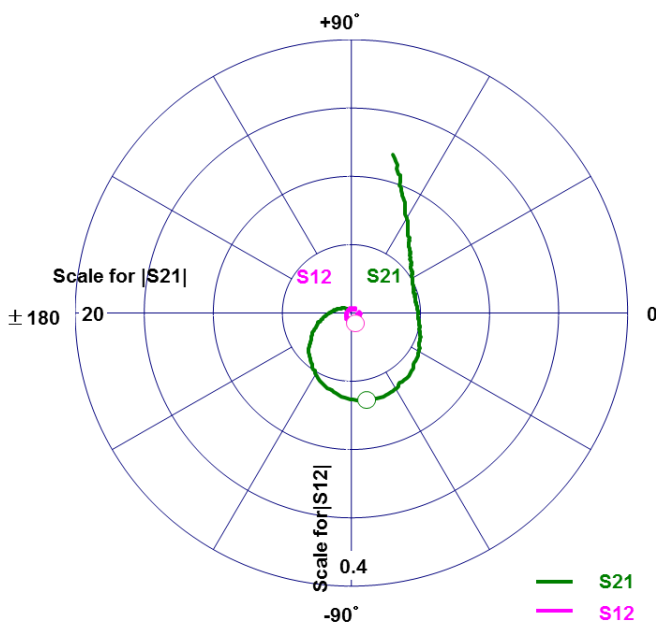


S-Parameters @VDS=50V, IDS(DC)=150mA, f=0.5 to 4.5GHz
 ZI = Zs = 50ohm Marker : 2.65GHz

- Reference DATA -



Freq. GHz	S11			S21			S12			S22		
	MAG	ANG		MAG	ANG		MAG	ANG		MAG	ANG	
0.5	0.92	-166.97		11.94	75.61		0.012	7.91		0.36	-66.06	
0.6	0.92	-171.86		9.99	69.46		0.011	-0.61		0.36	-72.82	
0.7	0.92	-175.96		8.77	63.69		0.013	-1.34		0.39	-79.87	
0.8	0.91	-179.22		7.80	58.39		0.011	-10.65		0.40	-85.74	
0.9	0.92	177.44		6.96	53.93		0.011	-6.82		0.43	-91.66	
1.0	0.91	175.02		6.39	49.25		0.011	-21.79		0.45	-95.93	
1.1	0.91	172.52		5.95	44.42		0.010	-12.97		0.46	-101.65	
1.2	0.91	170.13		5.59	39.25		0.011	-6.98		0.48	-106.24	
1.3	0.90	167.77		5.37	34.18		0.010	-16.43		0.51	-111.09	
1.4	0.90	165.04		5.06	29.42		0.010	-14.54		0.53	-115.25	
1.5	0.89	162.98		4.89	24.91		0.010	-13.69		0.55	-119.22	
1.6	0.88	160.67		4.82	20.00		0.009	-16.26		0.57	-122.69	
1.7	0.87	157.70		4.74	14.19		0.010	-11.22		0.59	-126.25	
1.8	0.85	154.60		4.77	8.42		0.011	-18.44		0.61	-130.51	
1.9	0.83	151.49		4.79	2.32		0.011	-19.84		0.63	-133.38	
2.0	0.81	147.78		4.85	-3.72		0.011	-21.50		0.66	-136.90	
2.1	0.78	144.29		5.01	-10.55		0.011	-22.29		0.67	-139.72	
2.2	0.73	139.79		5.28	-18.80		0.011	-21.43		0.70	-142.73	
2.3	0.67	135.62		5.58	-28.19		0.013	-25.02		0.73	-145.64	
2.4	0.58	131.48		5.88	-39.77		0.015	-33.77		0.76	-148.14	
2.5	0.45	129.66		6.27	-53.82		0.016	-45.57		0.79	-152.27	
2.6	0.30	139.63		6.55	-69.34		0.017	-59.65		0.84	-155.99	
2.7	0.28	173.93		6.34	-88.40		0.017	-75.19		0.86	-161.59	
2.8	0.43	-168.31		5.77	-107.48		0.015	-93.45		0.87	-167.43	
2.9	0.60	-169.67		4.90	-125.00		0.012	-115.01		0.87	-172.98	
3.0	0.72	-177.27		4.01	-140.21		0.011	-128.30		0.86	-177.50	
3.1	0.80	176.80		3.29	-150.47		0.010	-142.52		0.84	179.38	
3.2	0.85	170.63		2.69	-159.75		0.009	-150.81		0.83	175.87	
3.3	0.89	165.80		2.20	-167.28		0.006	169.60		0.82	172.97	
3.4	0.91	161.04		1.85	-174.71		0.005	156.63		0.81	169.82	
3.5	0.92	156.37		1.55	178.34		0.005	132.82		0.82	166.94	
3.6	0.93	152.88		1.33	173.02		0.005	125.35		0.81	164.15	
3.7	0.94	150.15		1.14	167.98		0.005	122.01		0.82	161.46	
3.8	0.95	146.68		0.98	163.17		0.005	90.61		0.82	158.23	
3.9	0.95	143.78		0.85	158.04		0.006	91.66		0.82	154.68	
4.0	0.95	141.11		0.74	152.59		0.007	77.98		0.82	151.63	
4.1	0.95	138.98		0.65	148.89		0.006	70.87		0.83	148.12	
4.2	0.96	135.29		0.58	144.29		0.008	58.80		0.83	145.14	
4.3	0.96	133.58		0.51	140.65		0.007	58.83		0.83	141.77	
4.4	0.95	131.30		0.45	135.78		0.007	47.70		0.84	138.62	
4.5	0.96	128.46		0.40	132.13		0.009	47.28		0.84	135.23	



ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	2
Machine Model (per JESD22-A115)	A
Charged-Device Model (per JESD22-C101)	C3

Ordering Information

Part Number	MOQ	MOU	Packing Style
SG26F30S-DT	2500pcs.	2500pcs.	Tape and Reel (16mm width Tape)
SG26F30S-DT1	500pcs.	500pcs.	Tape and Reel (16mm width Tape)
SG26F30S-D	20pcs.	20pcs.	Tray (4-inch)

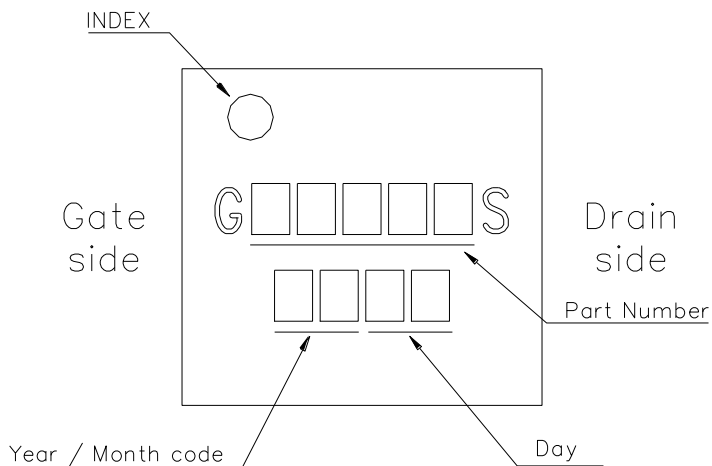
Note : *MOQ stands for Minimum Order Quantity.

*MOU stands for Minimum Order Unit size.

Moisture Sensitivity Level

Level	Floor Life	
	Time	Condition
2a	4weeks after open the package	≤30deg.C/60%RH

Package Markings



Year code

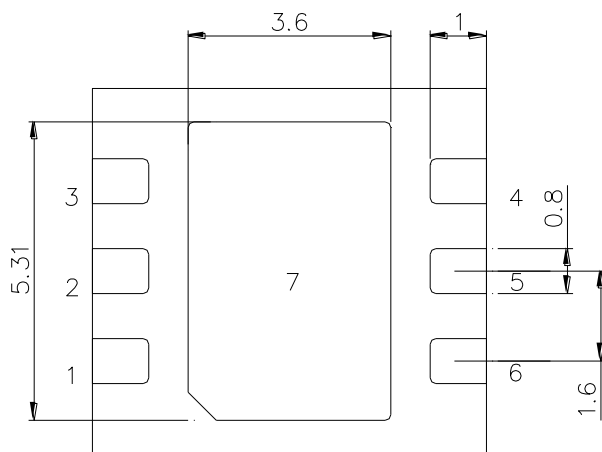
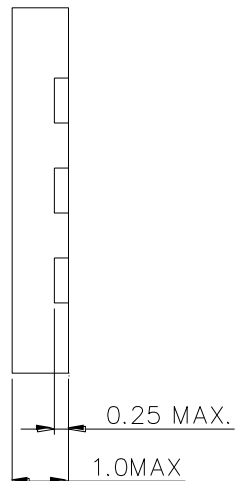
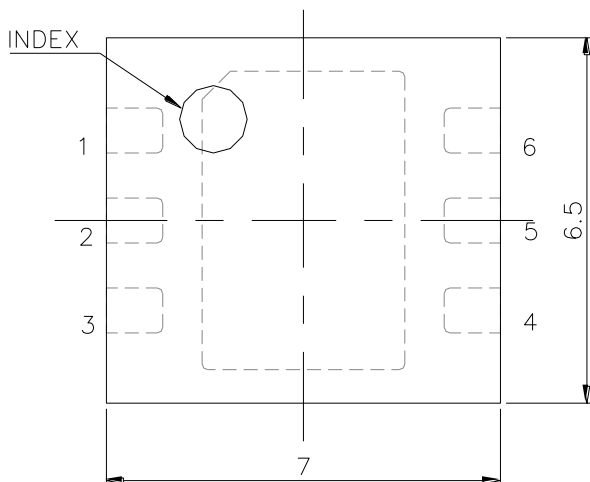
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023
Code	X	Y	Z	A	B	C	D	E	F

Note: Code letter is cycling 25 alphabet without Q.

Month code

Month	Jan.	Feb.	Mar.	Apr.	May	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
Code	H	M	N	P	R	S	T	U	W	X	Y	Z

Z2D Package Outline
Full Mold Plastic Package



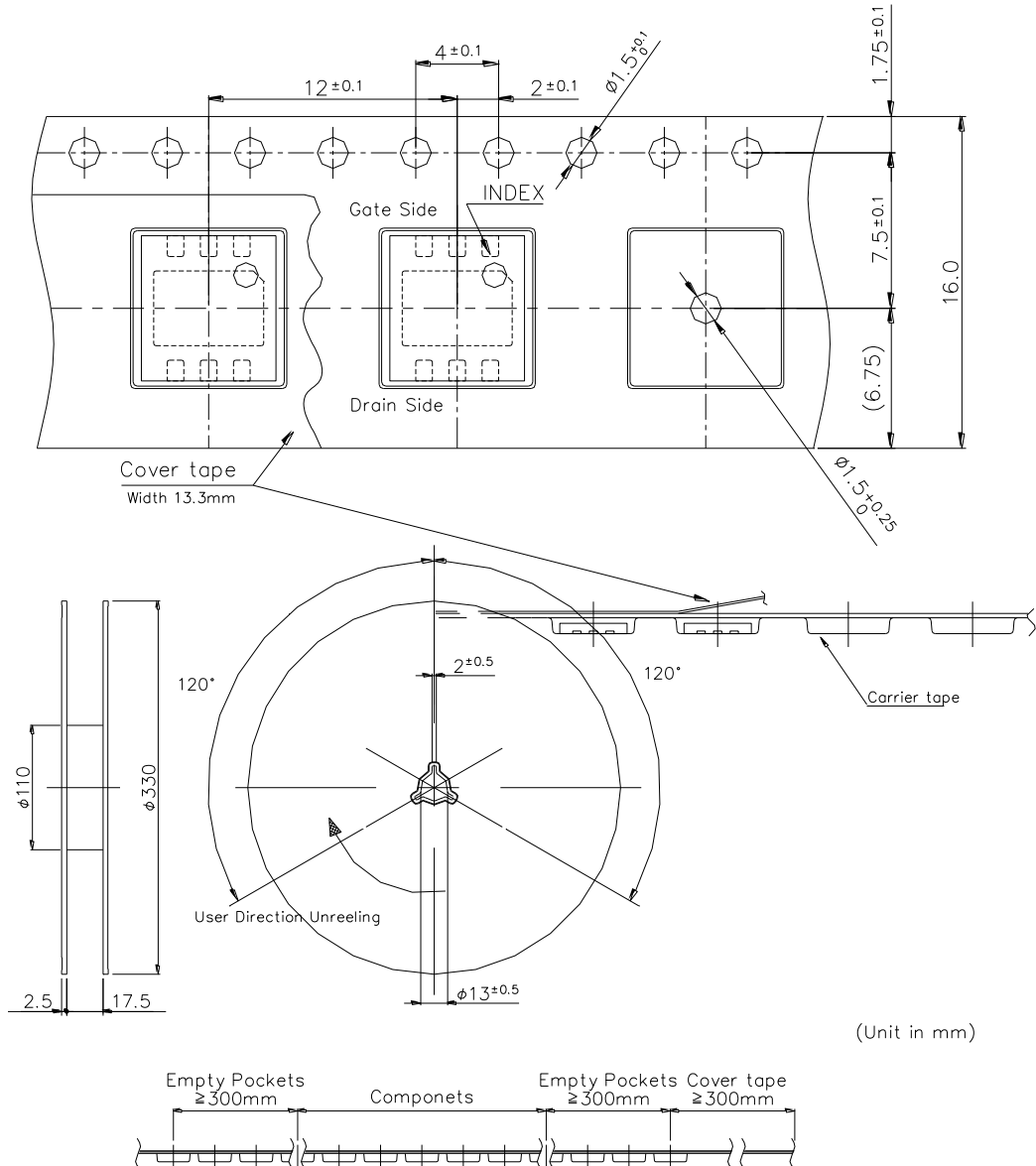
<Single Type>

- 1 : NC
- 2 : Gate
- 3 : NC
- 4 : NC
- 5 : Drain
- 6 : NC
- 7 : Source

Unit: mm
Tolerance : $\pm 0.15\text{mm}$

Index and Tape / Reel Configuration

(Part Number : SG26F30S-DT, SG26F30S-DT1)



Note : Baking of Tape & Reel is possible by following condition.

1. Recommended Baking Condition : 125deg.C, 8hours
2. Upper limit number of times : 5 times

* Reference standard : JIS standard(JIS C 0806-3)